

HMHAA280

HMHA2801

HMHA281

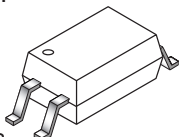
DESCRIPTION

The HMHA series consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a compact 4-pin mini-flat package. The lead pitch is 1.27 mm.

The HMHAA series consists of two gallium arsenide infrared emitting diodes, connected in inverse parallel, driving a single silicon phototransistor in a compact 4-pin mini-flat package.

FEATURES

- Compact 4-pin package (2.4 mm maximum standoff height)
- Half pitch leads for optimum board space savings
- Current Transfer Ratio in selected groups
HMHAA280: 50-600% HMHA2801: 80-600%
HMHA281: 50-600%
- Available in tape and reel quantities of 500 and 2500
- Applicable to Infrared Ray reflow (230°C Max, 30 seconds)
- BSI (File #8611/8612), CSA (File #1201524), UL (File #E90700) and VDE (File #136480) certified



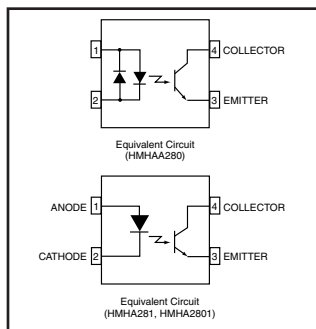
APPLICATIONS

HMHAA series

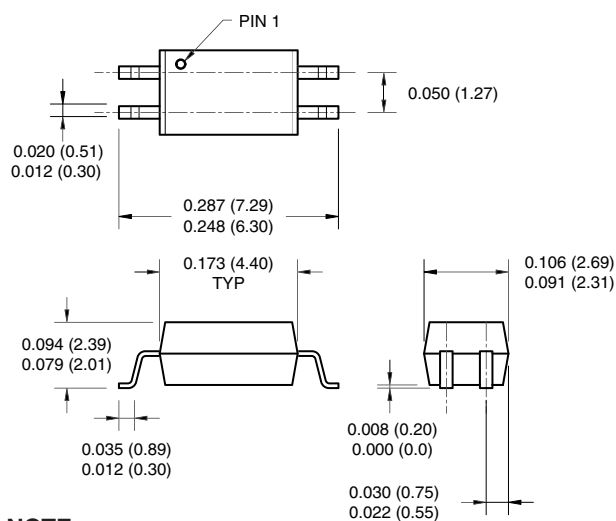
- AC line monitor
- Unknown polarity DC sensor
- Telephone line receiver

HMHA series

- Digital logic inputs
- Microprocessor inputs
- Power supply monitor
- Twisted pair line receiver
- Telephone line receiver



PACKAGE DIMENSIONS



NOTE

All dimensions are in inches (millimeters)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Units
TOTAL PACKAGE			
Storage Temperature	T _{STG}	-55 to +150	°C
Operating Temperature	T _{OPR}	-55 to +100	°C
EMITTER			
Continuous Forward Current	I _{F (avg)}	50	mA
Peak Forward Current (1 μs pulse, 300 pps.)	I _{F (pk)}	1	A
Reverse Input Voltage (HMA)	V _R	6	V
Power Dissipation	P _D	60	mW
Derate linearly (above 25°C)		0.6	mW/°C
DETECTOR			
Continuous Collector Current		50	mA
Power Dissipation	P _D	150	mW
Derate linearly (above 25°C)		1.5	mW/°C
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Collector Voltage	V _{ECO}	7	V

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)							
INDIVIDUAL COMPONENT CHARACTERISTICS							
Parameter	Test Conditions	Symbol	Device	Min	Typ**	Max	Unit
EMITTER Forward Voltage	$(I_F = 10 \text{ mA})$	V_F	HMHA281	1.0		1.3	V
			HMHA2801				
	$(I_F = \pm 5 \text{ mA})$		HMHAA280			1.4	
Reverse Current	$(V_R = 5 \text{ V})$	I_R	All			5	μA
DETECTOR							
Breakdown Voltage Collector to Emitter	$(I_C = 0.5 \text{ mA}, I_F = 0)$	BV_{CEO}	All	80			V
Emitter to Collector	$(I_E = 100 \mu\text{A}, I_F = 0)$	BV_{ECO}	All	7			
Collector Dark Current	$(V_{CE} = 80 \text{ V}, I_F = 0)$	I_{CEO}	All			100	nA
Capacitance	$(V_{CE} = 0 \text{ V}, f = 1 \text{ MHz})$	C_{CE}	All		10		pF

TRANSFER CHARACTERISTICS ($T_A = 25^\circ\text{C}$)							
Characteristic	Test Conditions	Symbol	Device	Min	Typ**	Max	Unit
DC Current Transfer Ratio	$(I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V})$	CTR	HMHAA280	50		600	%
	$(I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V})$		HMHA2801	80		600	
	$(I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V})$		HMHA281	50		600	
CTR Symmetry	$(I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V})$	—	HMHAA280	0.33		3.0	
Saturation Voltage	$(I_F = \pm 8 \text{ mA}, I_C = 2.4 \text{ mA})$	$V_{CE}(\text{SAT})$	HMHAA280			0.4	V
	$(I_F = 10 \text{ mA}, I_C = 2 \text{ mA})$		HMHA2801			0.3	
	$(I_F = 8 \text{ mA}, I_C = 2.4 \text{ mA})$		HMHA281			0.4	
Rise Time (Non-Saturated)	$(I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V})$ $(R_L = 100\Omega)$	t_r			3		μs
Fall Time (Non-Saturated)	$(I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V})$ $(R_L = 100\Omega)$	t_f			3		

ISOLATION CHARACTERISTICS							
Characteristic	Test Conditions	Symbol	Device	Min	Typ**	Max	Unit
Steady State Isolation Voltage	(1 Minute)	V_{ISO}	All	2500			VRMS

** All typicals at $T_A = 25^\circ\text{C}$

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TYPICAL PERFORMANCE CURVES

Fig. 1 Forward Current vs. Forward Voltage

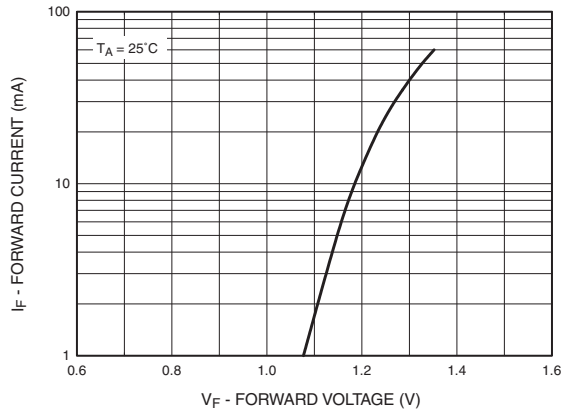


Fig. 2 Collector Current vs. Forward Current

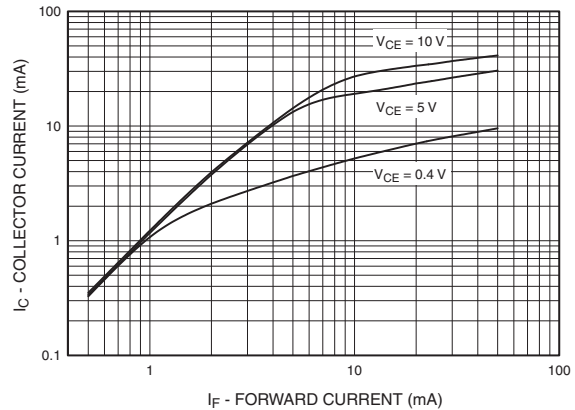


Fig. 3 Current Transfer Ratio vs. Forward Current

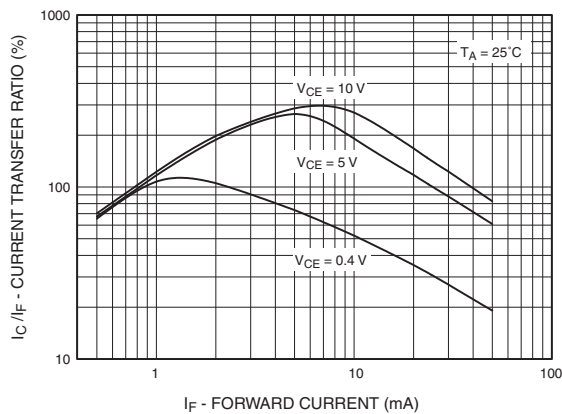


Fig. 4 Normalized CTR vs. Temperature

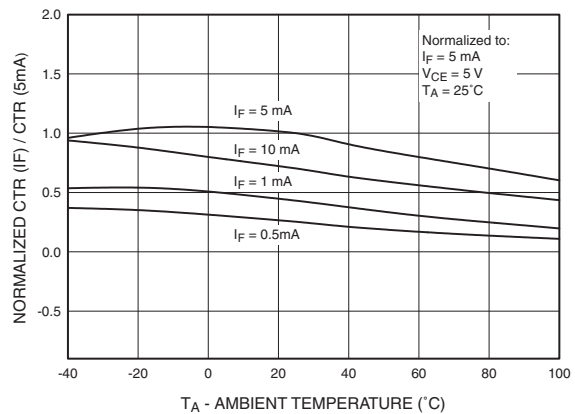
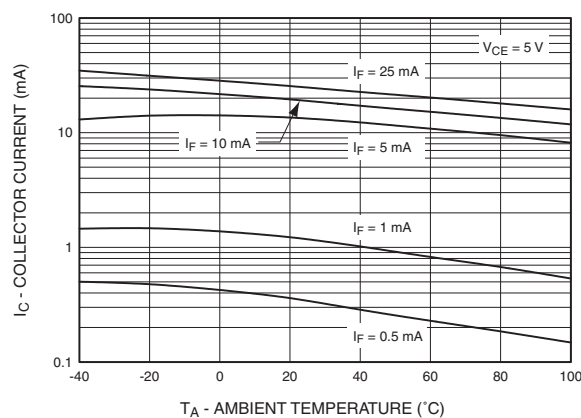


Fig. 5 Collector Current vs. Temperature



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Fig. 6 Collector Current vs. Collector-Emitter Voltage

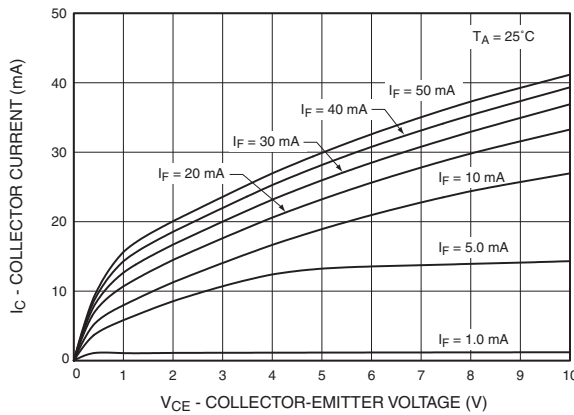


Fig. 7 Collector Current vs. Collector-Emitter Voltage

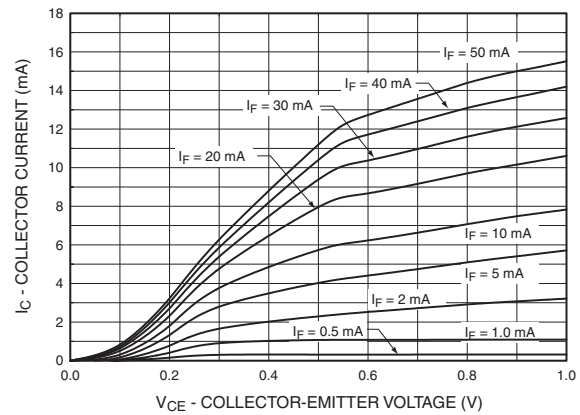


Fig. 8 Collector Dark Current vs. Temperature

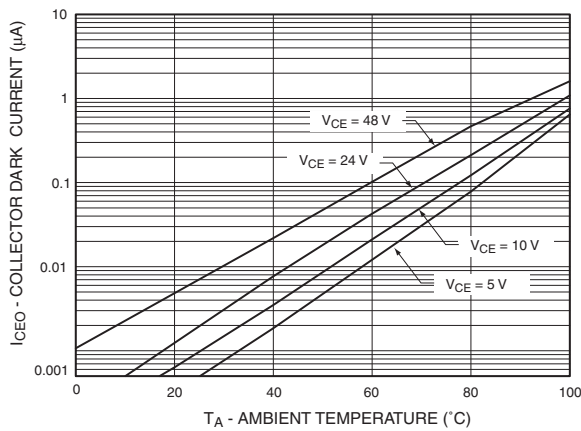


Fig. 9 Switching Time vs. Load Resistance

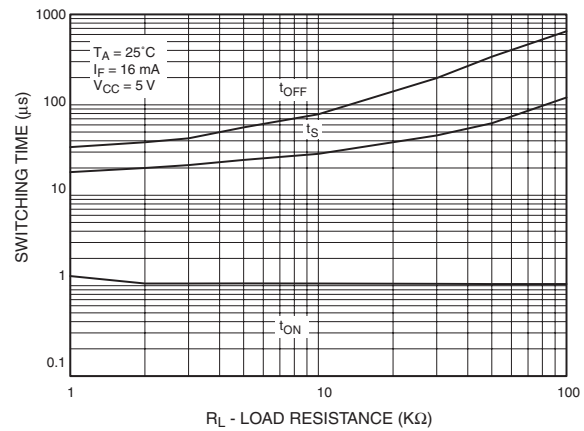
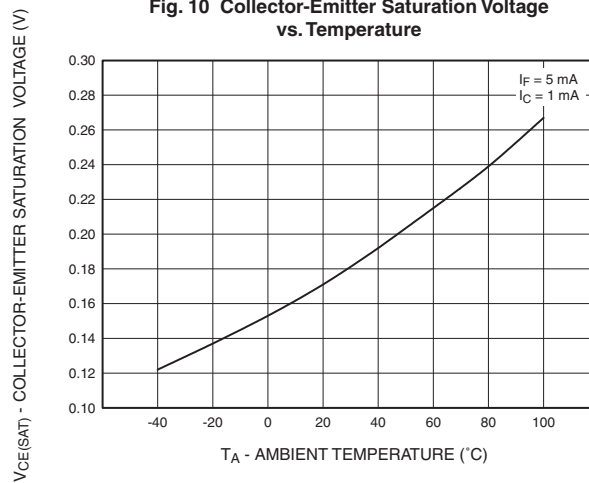


Fig. 10 Collector-Emitter Saturation Voltage vs. Temperature



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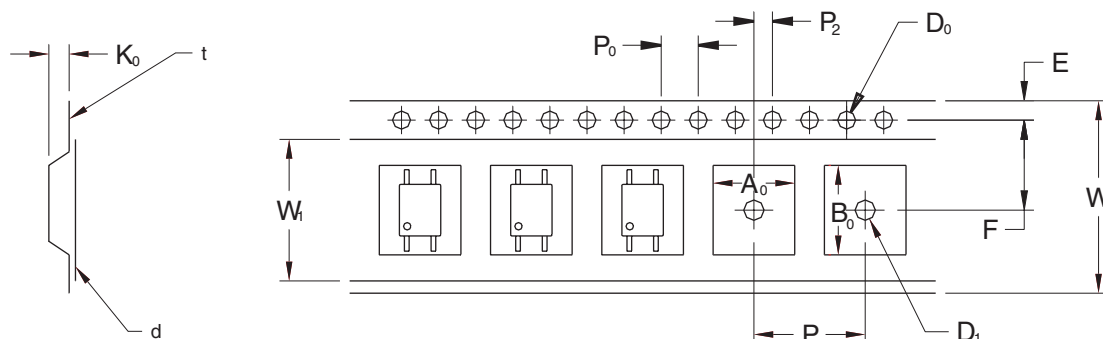
ORDERING INFORMATION

Option	Description
V	VDE Approved
R1	Tape and Reel (500 units)
R2	Tape and Reel (2500 units)
R1V	Tape and Reel (500 units) and VDE Approved
R2V	Tape and Reel (2500 units) and VDE Approved

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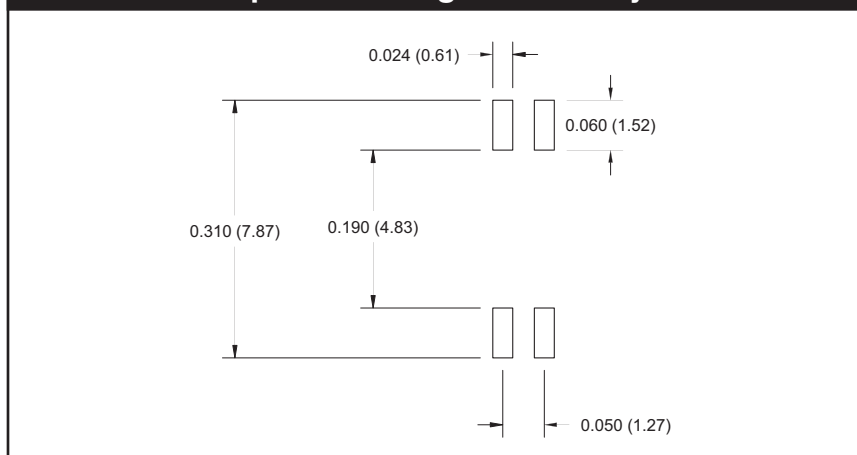
		1.27 Pitch
Description	Symbol	Dimensions (mm)
Tape Width	W	12.00±0.4
Tape Thickness	t	0.30±0.20
Sprocket Hole Pitch	P_0	4.00±0.20
Sprocket Hole Dia.	D_0	1.55±0.20
Sprocket Hole Location	E	1.75±0.20
Pocket Location	F	5.50±0.20
	P_2	2.00±0.20
Pocket Pitch	P	8.00±0.20
Pocket Dimension	A_0	4.40±0.20
	B_0	7.30±0.20
	K_0	2.30±0.20
Pocket Hole Dia.	D_1	1.55±0.20
Cover Tape Width	W_1	9.20
Cover Tape Thickness	d	0.065±0.02
Max. Component Rotation or Tilt		20° max
Devices Per Reel	R1	500
	R2	2500
Reel Diameter	R1	178 mm (7")
	R2	330 mm (13")

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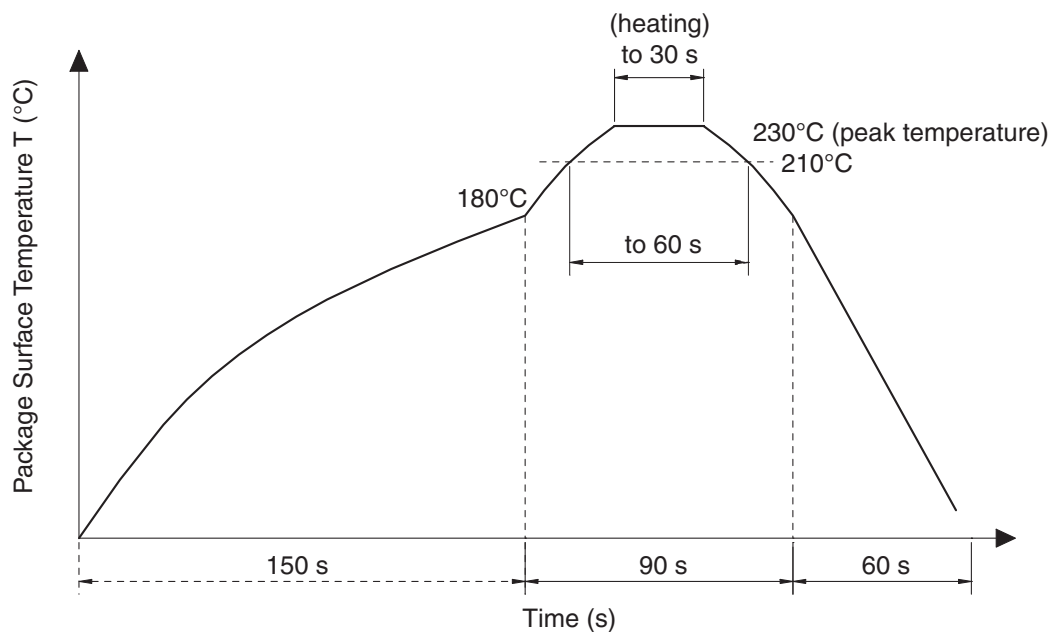
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Footprint Drawing for PCB Layout



Recommended Infrared Reflow Soldering Profile



- Peak reflow temperature: 230°C (package surface temperature) for 30 seconds
- Time of temperature higher than 210°C: 60 seconds or less
- One time soldering reflow is recommended

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